



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: M. Nandakumar et al.

Examiner: Edgardo Ortiz

Serial No.: 09/876,292 ✓

Art Unit: 2815

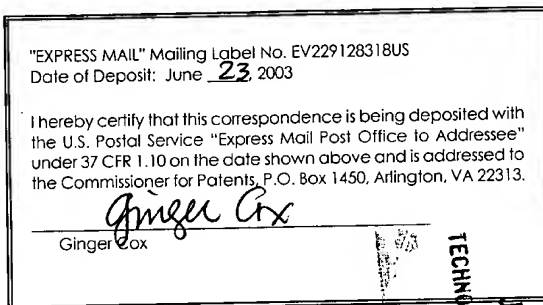
Filed: 06/07/2001 ✓

Docket: TI-31089

For: ADDITIONAL N-TYPE LDD/POCKET IMPLANT FOR IMPROVING  
SHORT-CHANNEL NMOS ESD ROBUSTNESS

June 23, 2003

Commissioner for Patents  
P.O. Box 1450  
Arlington, VA 22313-1450



Sir:

AMENDMENT PURSUANT TO 37 CFR 1.115

Responsive to the Office Action of March 25, 2003, favorable reconsideration and allowance of the application are respectfully requested, in view of the following comments.

The rejection of claims 1-11 for double patenting over U.S. 6,452,236 in view of Yang (U.S. 6,040,603) is respectfully traversed because 1) Yang is misdescribed by the Office Action, and mistakenly relied upon for the opposite of what it actually teaches; and 2) therefore the references are improperly combined.

Note specifically in Yang that region 309 surrounding the source and drain has the same conductivity type as the source and drain. But in Applicants' invention the region surrounding the source and drain has the opposite conductivity type.

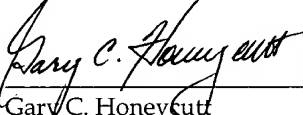


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It is clearly improper to ignore conductivity types. It is clearly improper to contend that an N-type region suggests a P-type region. Yang expressly teaches that region 309 must have the same conductivity type as the source and drain. Applicants' claims expressly require the opposite. The function of Applicants' region is incompatible with the function of Yang's region 309.

Therefore the rejection is improper and should be withdrawn. Applicants now believe the application is in condition for allowance.

Respectfully submitted,

  
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